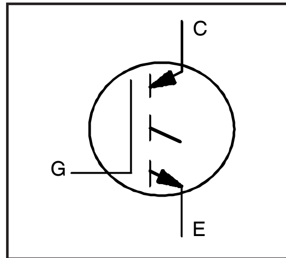
International
IOR Rectifier

PD- 91772B

IRG4CC40KB

IRG4CC40KB IGBT Die in Wafer Form



600 V
Size 4
Ultra-Fast Speed
6'' Wafer

Electrical Characteristics (Wafer Form)

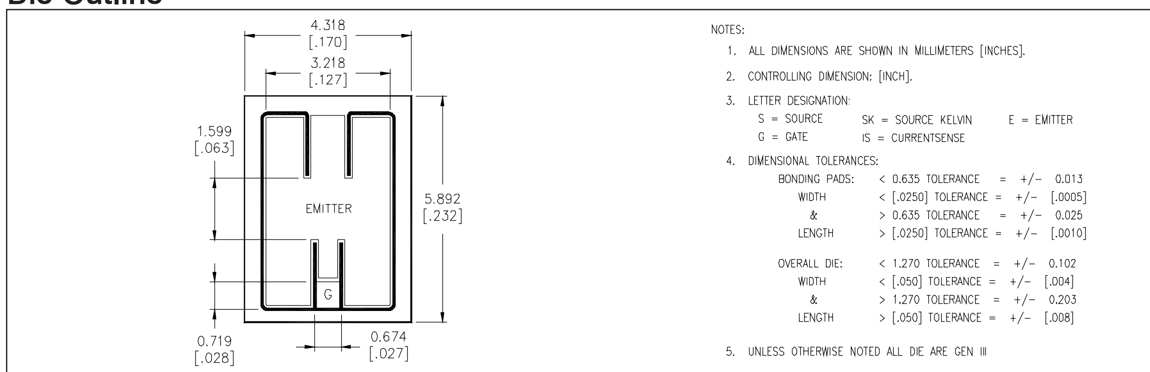
Parameter	Description	Guaranteed (Min/Max)	Test Conditions
$V_{CE\ (on)}$	Collector-to-Emitter Saturation Voltage	2.4V Max.	I_C = 10A, T_J = 25°C, V_{GE} = 15V
$V_{(BR)CES}$	Colletor-to-Emitter Breakdown Voltage	600V Min.	T_J = 25°C, I_{CES} = 250µA, V_{GE} = 0V
$V_{GE(th)}$	Gate Threshold Voltage	3.0V Min., 6.0V Max.	V_{GE} = V_{CE} , T_J =25°C, I_C =250µA
I_{CES}	Zero Gate Voltage Collector Current	250µA Max.	T_J = 25°C, V_{CE} = 600V
I_{GES}	Gate-to-Emitter Leakage Current	± 1.1µA Max.	T_J = 25°C, V_{GE} = +/- 20V

Mechanical Data

Norminal Backmetal Composition, Thickness:	Cr-Ni-Ag (1kA-2kA-2.5kA)
Norminal Front Metal Composition, Thickness:	99% Al, 1% Si (4 microns)
Dimensions:	0.170" x 0.232"
Wafer Diameter:	150mm, with std. < 100 > flat
Wafer thickness:	.015" + / -.003"
Relevant Die Mechanical Dwg. Number	01-5231
Minimum Street Width	100 Microns
Reject Ink Dot Size	0.25mm Diameter Minimum
Ink Dot Location	Consistent throughout same wafer lot
Recommended Storage Environment:	Store in original container, in dessicated nitrogen, with no contamination
Recommended Die Attach Conditions:	For optimum electrical results, die attach temperature should not exceed 300C

Reference Standard IR packaged part (for design) : IRG4PC40K

Die Outline



09/27/07